

## General Description

SFGMOS<sup>®</sup> MOSFET is based on Oriental Semiconductor's unique device design to achieve low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. The low  $V_{th}$  series is specially designed to use in synchronous rectification power systems with low driving voltage.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery



## Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

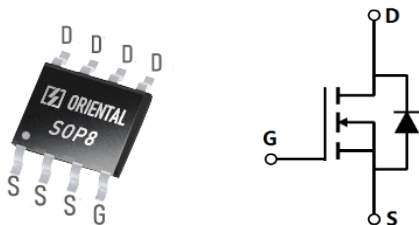
## Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	100	V
$I_{D, pulse}$	48	A
$R_{DS(ON), max} @ V_{GS}=10V$	12	m $\Omega$
$Q_g$	32.1	nC

## Marking Information

Product Name	Package	Marking
SFG10S12BF	SOP8	SFG10S12B

## Package & Pin information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	100	V
Gate source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_D$	12	A
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	48	A
Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_S$	12	A
Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	48	A
Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$	$P_D$	4	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	65	mJ
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^{\circ}\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	31	$^{\circ}\text{C/W}$

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	100			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	1.5		2.5	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		9.2	12.0	m $\Omega$	$V_{GS}=10\text{ V}, I_D=12\text{ A}$
Drain-source on-state resistance	$R_{DS(ON)}$		12.0	16.0	m $\Omega$	$V_{GS}=4.5\text{ V}, I_D=9\text{ A}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}$

### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		1918		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=100\text{ kHz}$
Output capacitance	$C_{oss}$		353		pF	
Reverse transfer capacitance	$C_{rss}$		10.6		pF	
Turn-on delay time	$t_{d(on)}$		20.1		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=50\text{ V}$ , $R_G=2\ \Omega$ , $I_D=10\text{ A}$
Rise time	$t_r$		4.5		ns	
Turn-off delay time	$t_{d(off)}$		44.3		ns	
Fall time	$t_f$		8.5		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		32.1		nC	$V_{GS}=10\text{ V}$ , $V_{DS}=50\text{ V}$ , $I_D=10\text{ A}$
Gate-source charge	$Q_{gs}$		6.1		nC	
Gate-drain charge	$Q_{gd}$		8.1		nC	
Gate plateau voltage	$V_{plateau}$		3.3		V	

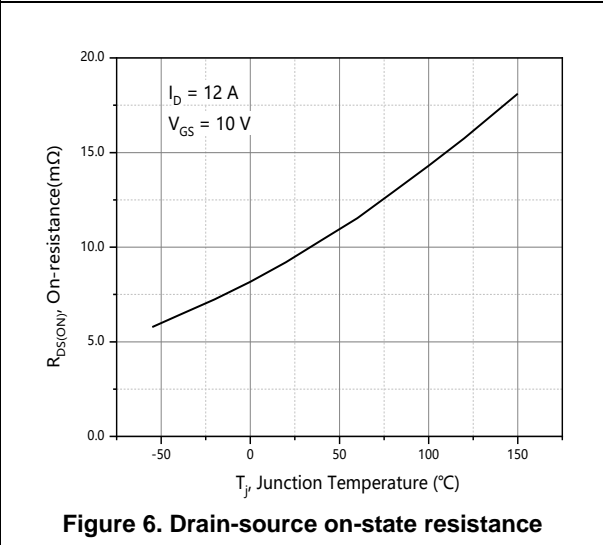
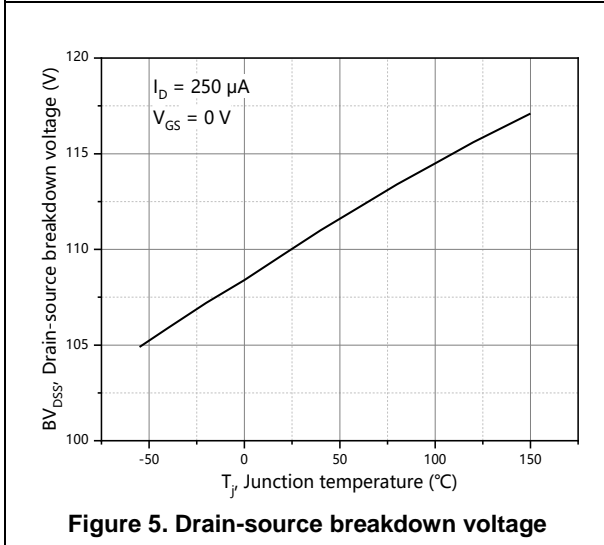
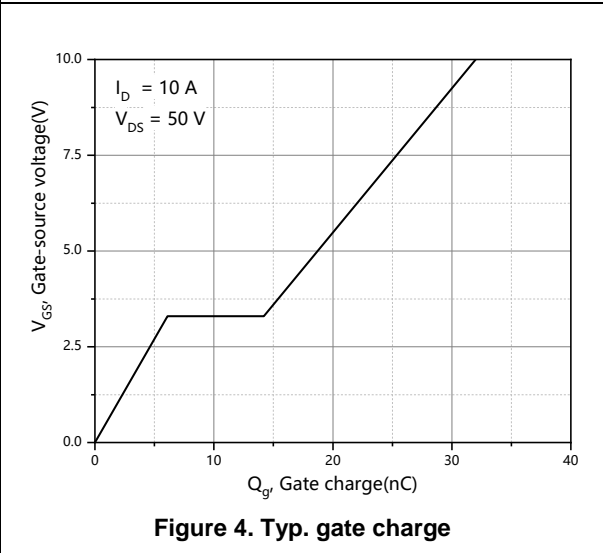
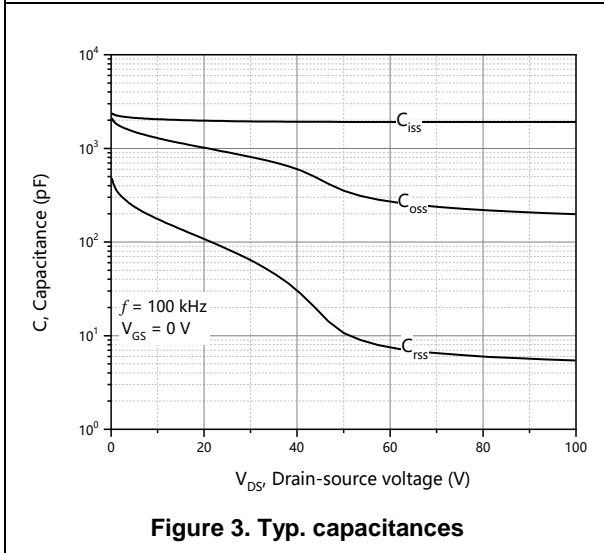
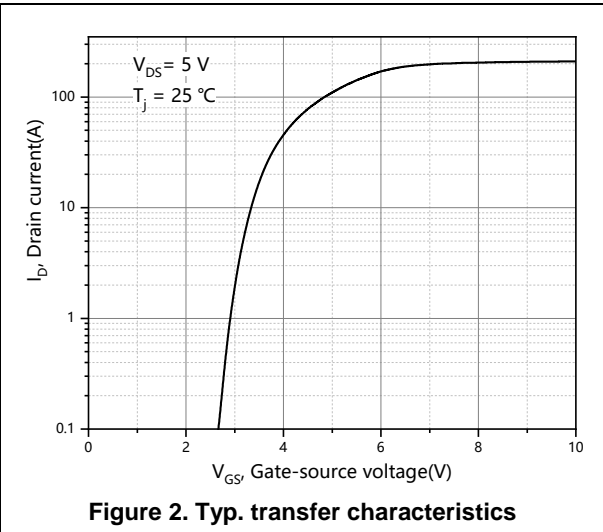
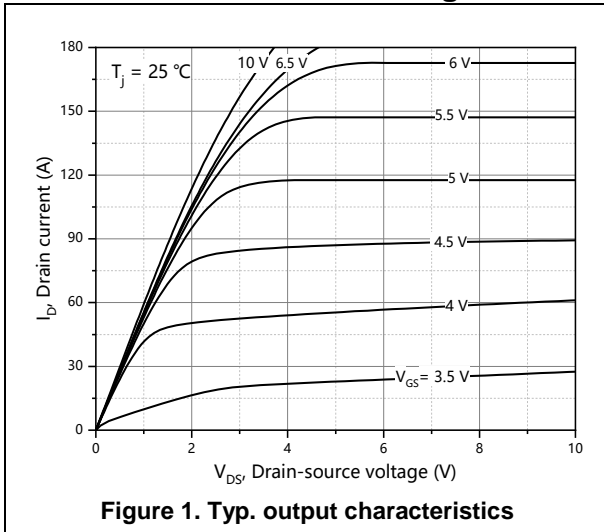
### Body Diode Characteristics

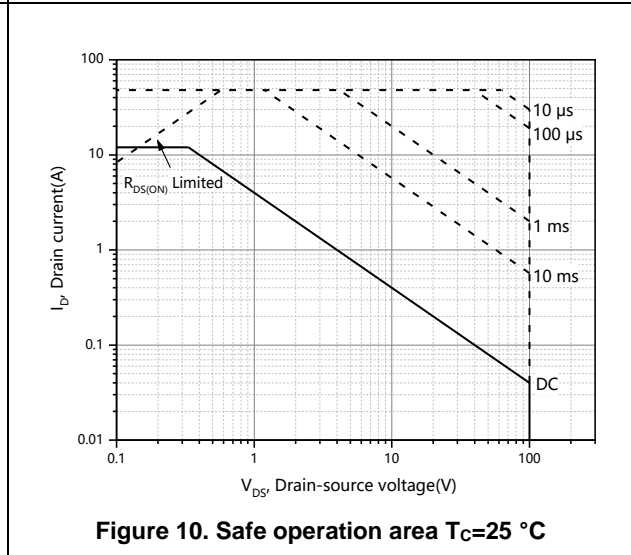
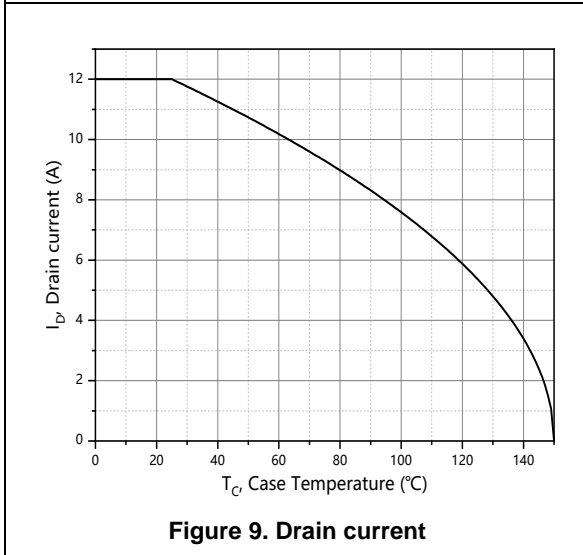
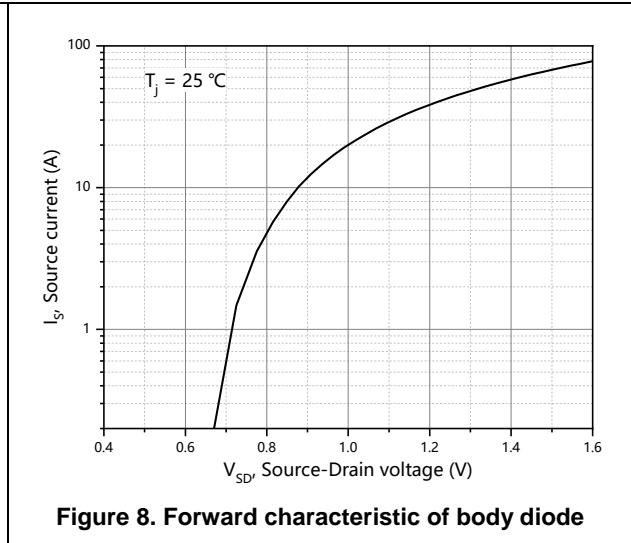
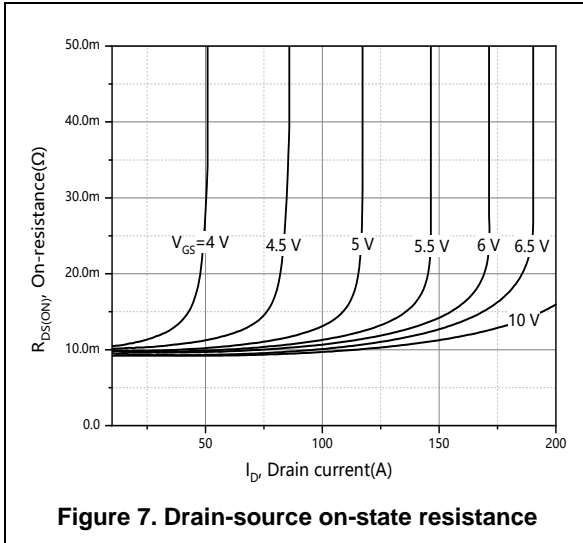
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=12\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		51.0		ns	$V_R=50\text{ V}$ , $I_S=10\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		86.8		nC	
Peak reverse recovery current	$I_{rrm}$		2.9		A	

### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=0.3\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

**Electrical Characteristics Diagrams**





**Test circuits and waveforms**



**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

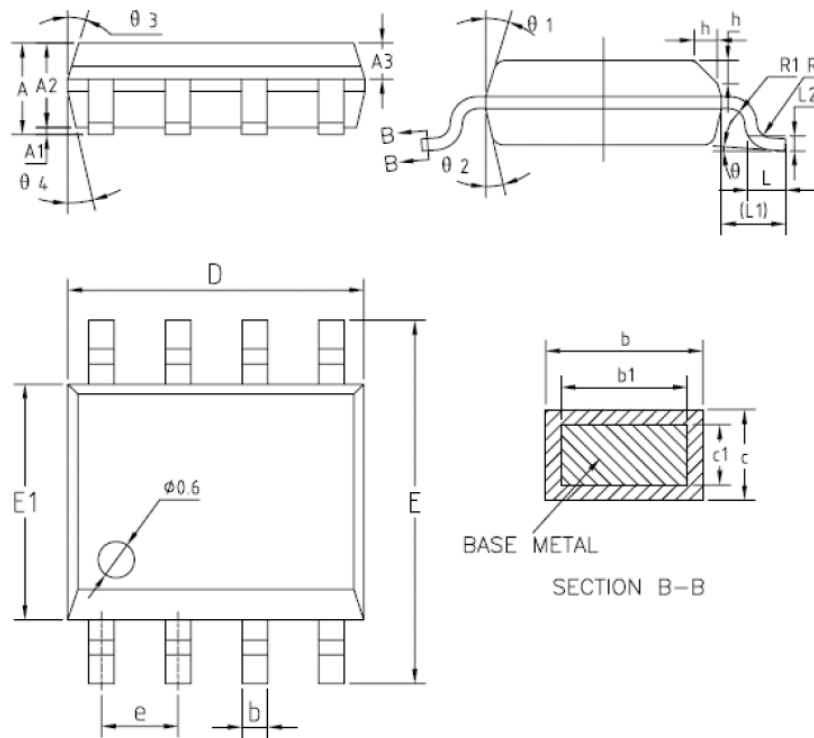


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

**Package Information**



Symbol	mm		
	Min	Nom	Max
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	-	0.51
L1	1.04REF		
L2	0.25BSC		
b1	0.37	0.42	0.47
c	0.18	-	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
R	0.07	-	-
R1	0.07	-	-
h	0.30	0.40	0.50
$\theta$	0°	-	8°
$\theta 1$	15°	17°	19°
$\theta 2$	11°	13°	15°
$\theta 3$	15°	17°	19°
$\theta 4$	11°	13°	15°

Version 1: SOP8-K package outline dimension

## Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
SOP8-K	2500	2	5000	6	30000

## Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG10S12BF	SOP8	yes	yes	yes

## Legal Disclaimer

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